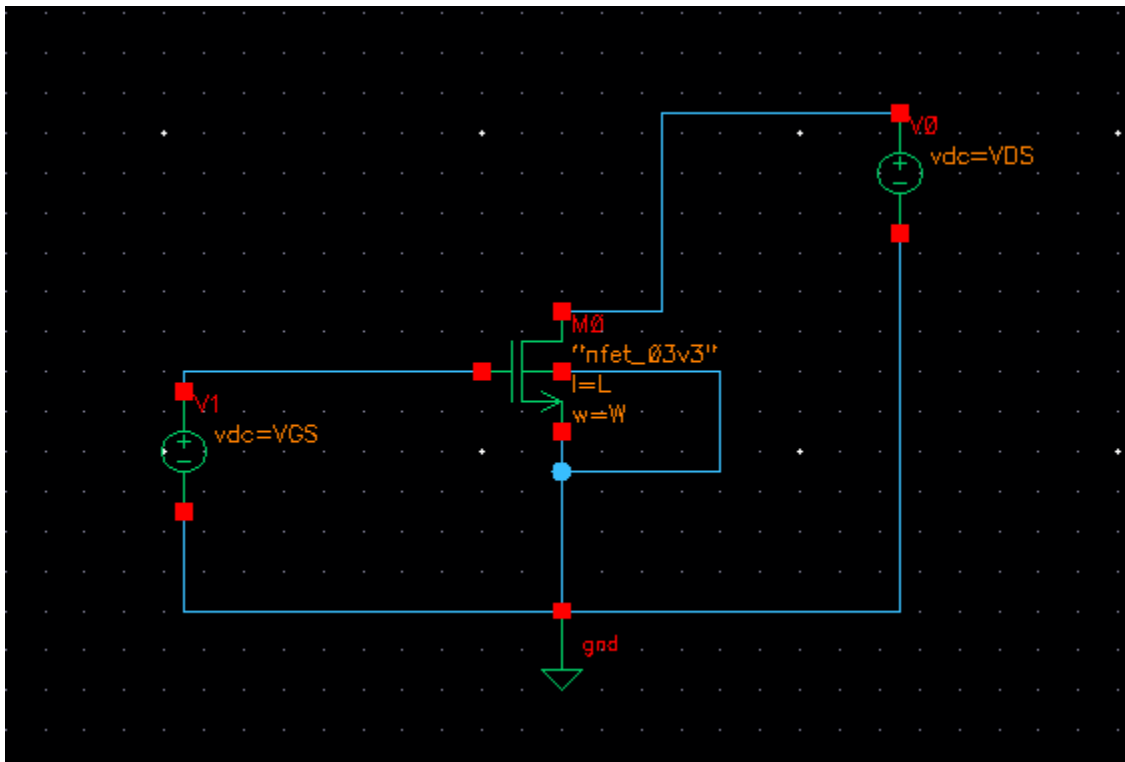


Analog IC Design – Cadence Tools

Lab 03

Cascode Amplifier

Part 1: Sizing Chart:



spec	0.18um CMOS
L	0.5um
V*	160mV
Supply	1.8VA
Current consumption	10 μA

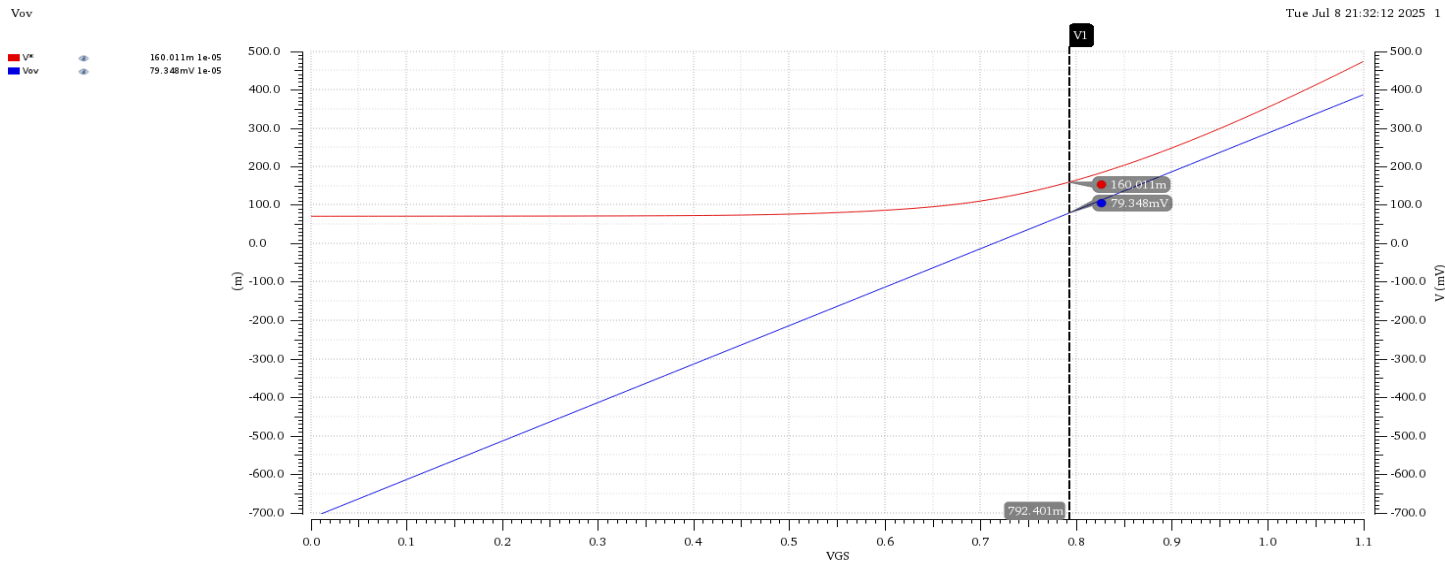


Figure 1: V^* and V_{ov} VS V_{gs}

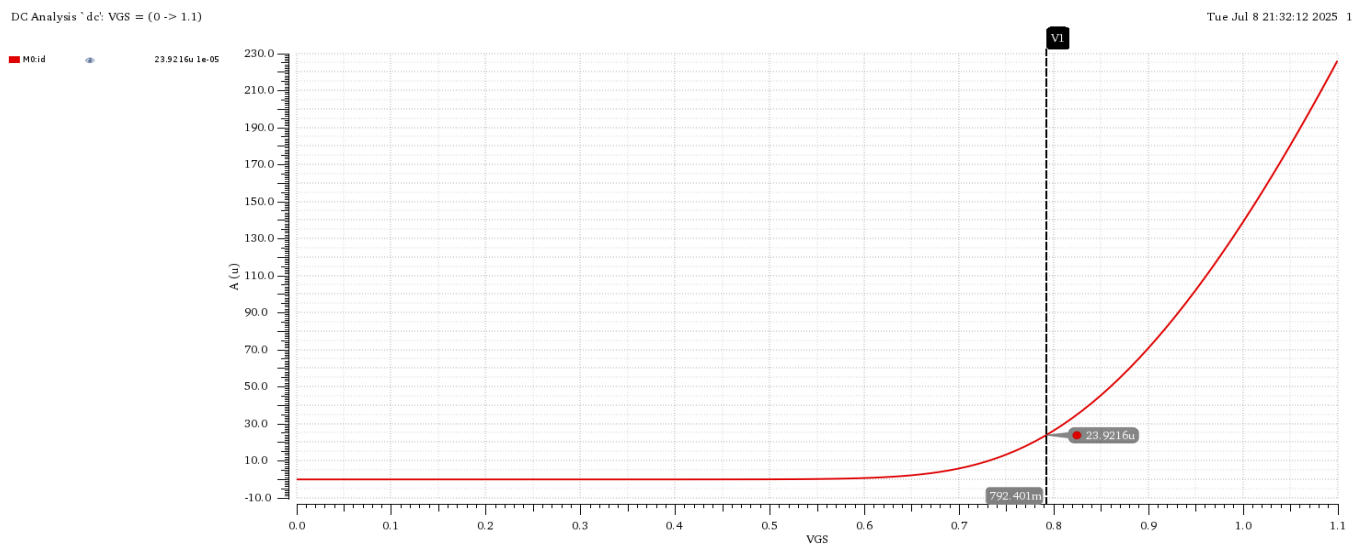


Figure 2: I_D VS V_{gs}

DC Analysis 'dc': VGS = (0 -> 1.1)

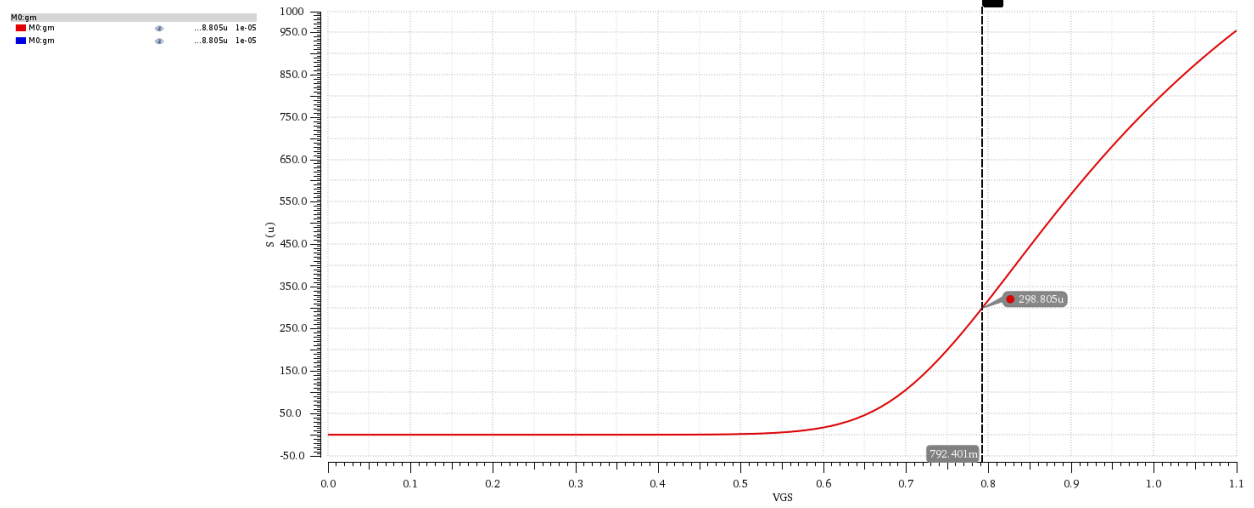


Figure 3: gm VS Vgs

DC Analysis 'dc': VGS = (0 -> 1.1)

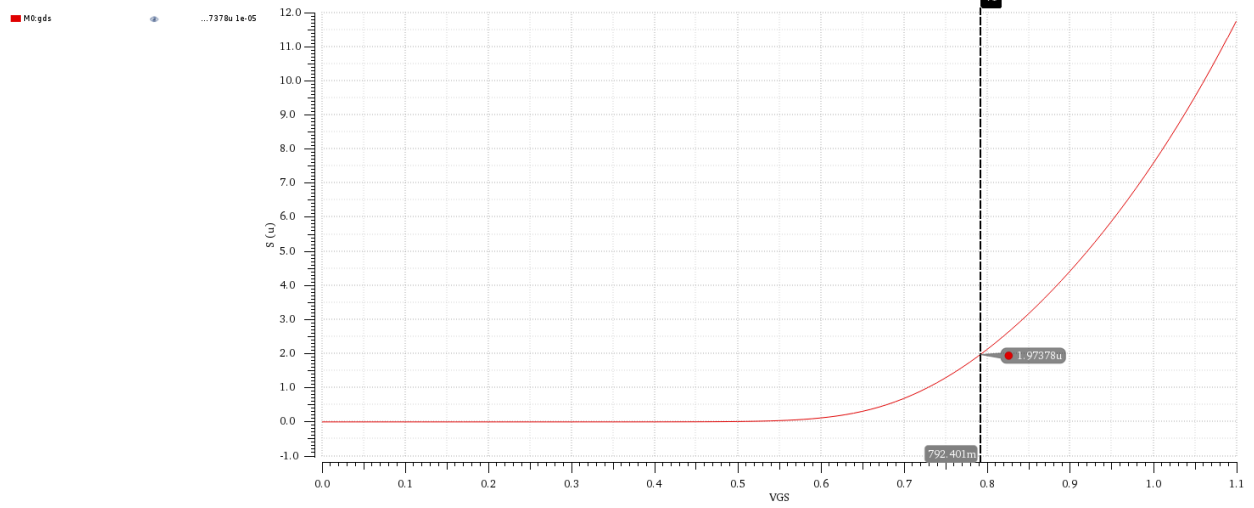


Figure 4:gds VS Vgs

1-

V^*	160 mV
V_{ovQ}	79.348 mV
V_{GSQ}	792.401 mV
I_{Dx}	23.9316 μA
g_{mx}	298.805 μS
g_{dsx}	1.79378 μS

2-

W	Id
10 μm	23.9316 μA
4.1786 μm	10 μA
g_m	0.1249 mS
g_{ds}	0.7495 μS
r_o	1.3341 M Ω

PART 2: Cascode for Gain :

1. OP Analysis :

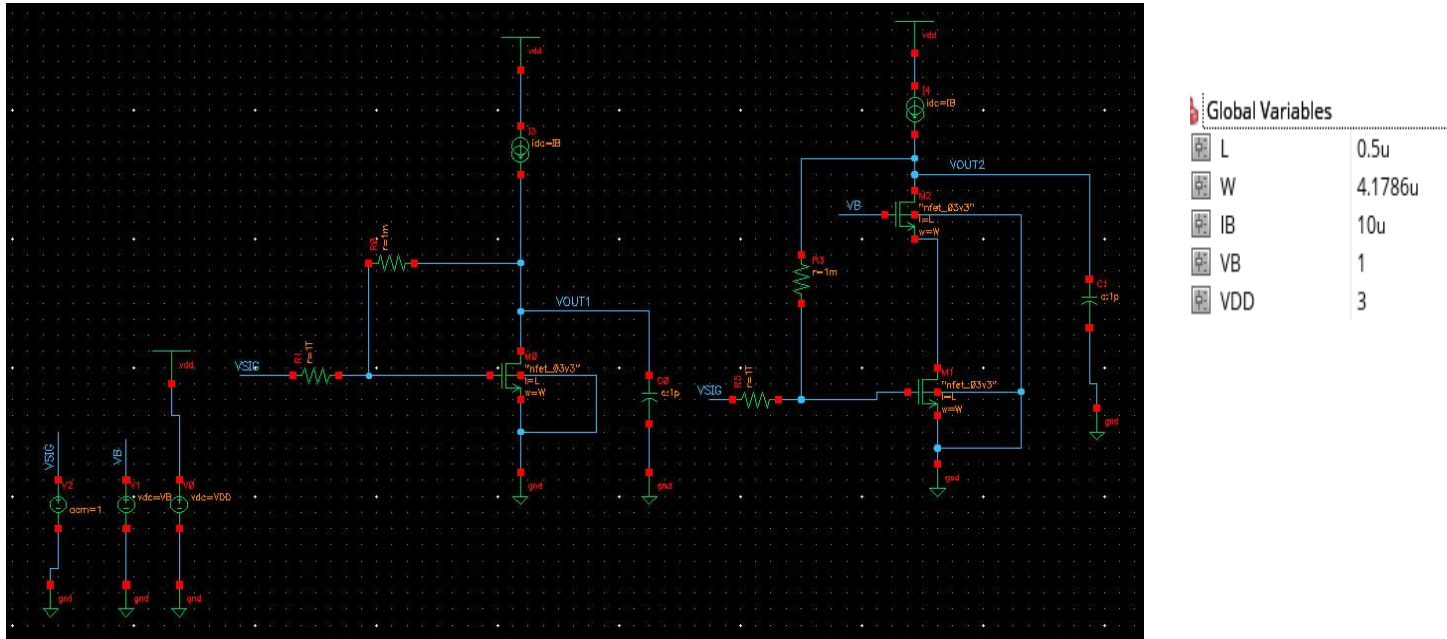


Figure 5:schematic

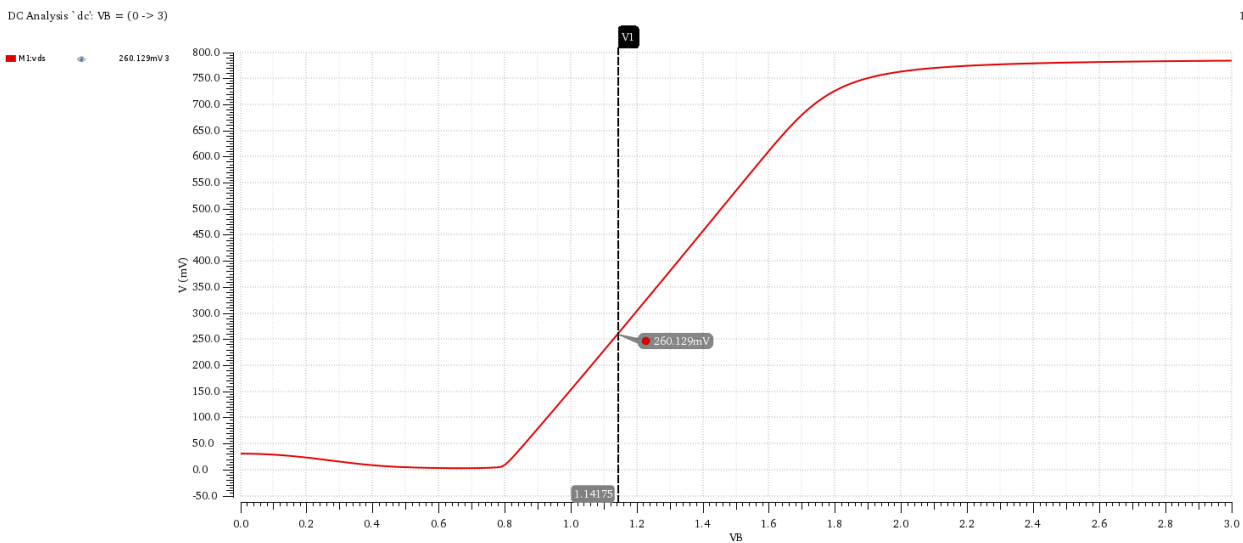


Figure 6:VB VS VDS

AS SHOWN VB from graph = 1.14175 V

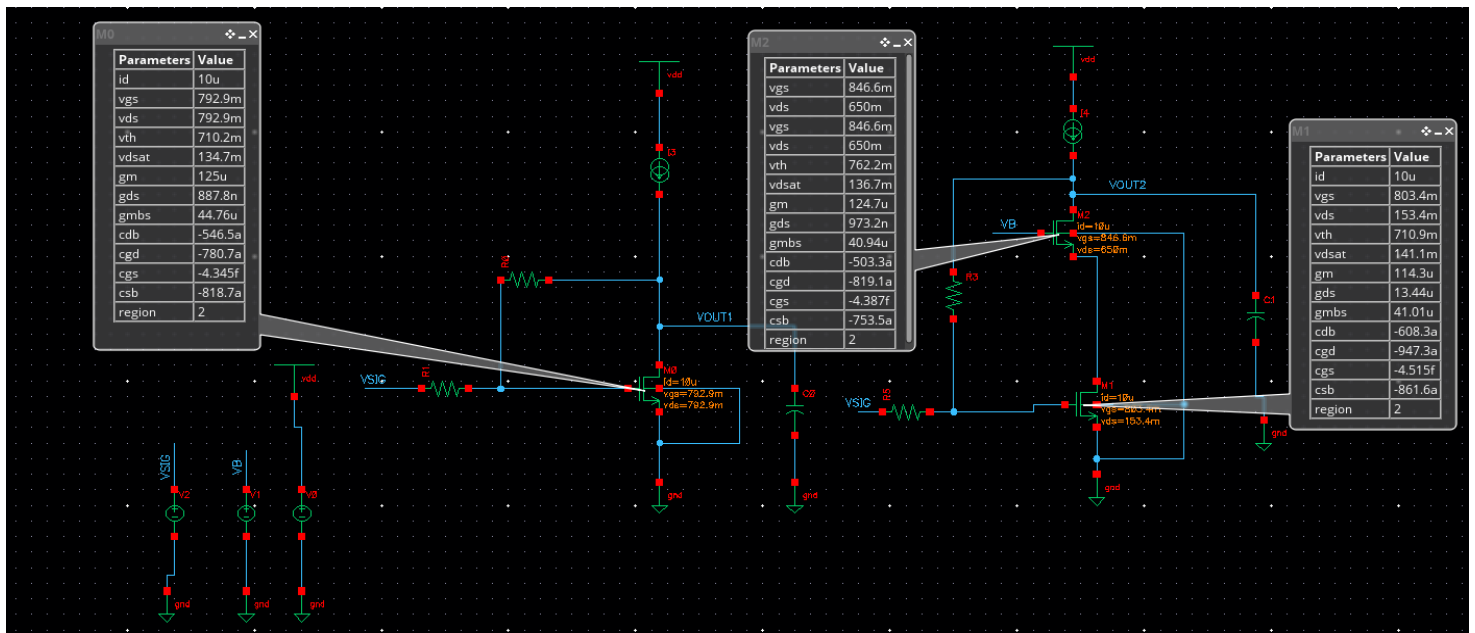


Figure 7: schematic with annotation

As we see all transistors work in **region (2) “saturation region”**

Do all transistors have the same vth? Why?

Transistors have not the same Vth The threshold voltage (V_{th}) of a transistor can vary due to several factors, even among transistors of the same type. Here are the key reasons for the observed differences in V_{th} in your data:

1. Process Variations

Manufacturing Tolerances: During fabrication, slight variations in doping concentrations, oxide thickness, or channel length/width can occur, leading to differences in V_{th} .

Random Dopant Fluctuations (RDF): Random distribution of dopant atoms in the channel can cause localized variations in V_{th} .

2- Body Effect (Substrate Bias)

The threshold voltage depends on the voltage between the source and the substrate (V_{SB}). If the substrate bias varies, V_{th} will also change

3-Drain-Induced Barrier Lowering (DIBL)

At higher drain-to-source voltages (V_{DS}), the electric field from the drain can lower the potential barrier in the channel, effectively reducing V_{th} . This is more pronounced in short-channel devices.

What is the relation (\ll , $<$, $=$, $>$, \gg) between gm and gds?

gm>>gds

What is the relation (\ll , $<$, $=$, $>$, \gg) between gm and gmb?

gm>gmb

What is the relation (\ll , $<$, $=$, $>$, \gg) between cgs and cgd?

cgs>cgd

What is the relation (\ll , $<$, $=$, $>$, \gg) between csb and cdb?

Csb>cdb

The dc gain,BW, UFG and GBW of both circuits from simulation



Test	Output	Nominal	Spec	Weight	Pass/Fail
LAST_LAB:last:1	VOUT1_DB				
LAST_LAB:last:1	GAIN DB 1	42.97			
LAST_LAB:last:1	GAIN MAG 1	140.8			
LAST_LAB:last:1	BW1	140.8k			
LAST_LAB:last:1	GBW 1	19.88M			
LAST_LAB:last:1	UFG1	19.84M			
LAST_LAB:last:1	VOUT2_DB				
LAST_LAB:last:1	GAIN DB 2	77.15			
LAST_LAB:last:1	GAIN MAG	7.205k			
LAST_LAB:last:1	BW2	2.655k			
LAST_LAB:last:1	GBW2	19.18M			
LAST_LAB:last:1	UFG2	19.27M			

Figure 8: table of requirements

Bode plot :

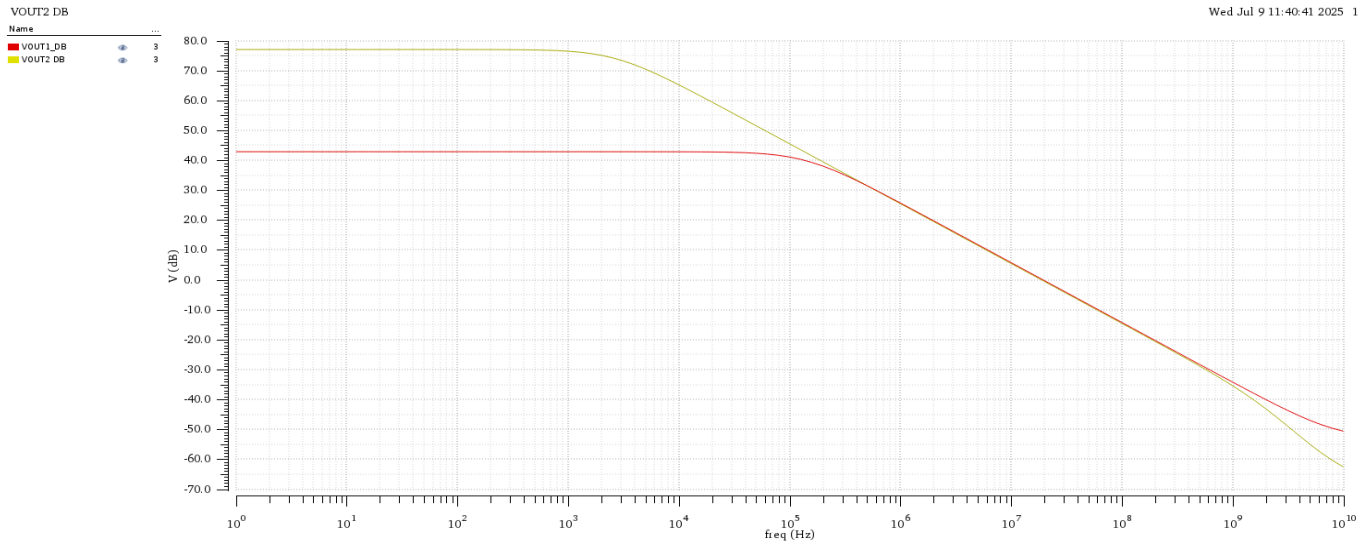


Figure 9:vout1db_vout2db VS freq

Hand analysis:

In a common source amplifier , dc gain (mag) given by :

$$A_V = g_m \times r_o = g_m \times \frac{1}{g_{ds}} = 140.797$$

But In a cascode amplifier , dc gain (mag) given by:

$$A_V = g_m \times R_{out} = -g_{m1} \times r_{o2}(g_{m2} + g_{mb2})r_{o1} \approx 7.45 \text{ K}$$

	CS	Cascode
DC gain hand analysis	140.797	7.45 K
DC gain from simulation	140.8	7.205 K

COMMENT

The **cascode amplifier** provides **much higher DC gain** than a common-source (CS) stage because it **boosts the** output resistance.

CS Amplifier: Gain is limited by $r_{o1}r_{o1}$ (drain-source resistance of single transistor).

Cascode Amplifier: Adds a second transistor to multiply r_{oro} , dramatically increasing output resistance and gain.